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FDP023N08B N-Channel PowerTrench[®] MOSFET 75 V, 242 A, 2.35 m Ω

Features

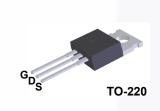
- $R_{DS(on)}$ = 1.96 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- Low FOM R_{DS(on)}*Q_G
- Low Reverse Recovery Charge, Qrr
- Soft Reverse Recovery Body Diode
- Enables Highly Efficiency in Synchronous Rectification
- · Fast Switching Speed
- 100% UIL Tested
- RoHS Compliant

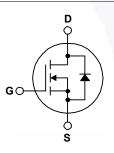
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- DC motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverte





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDP023N08B_F102	Unit
V _{DSS}	Drain to Source Voltage		75	V
V _{GSS}	Gate to Source Voltage		±20	V
I _D [Drain Current	- Continuous (T _C = 25 ^o C, Silicon Limited)	242*	A
		- Continuous (T _C = 100 ^o C, Silicon Limited)	171*	
		- Continuous (T _C = 25 ^o C, Package Limited)	120	
I _{DM}	Drain Current	- Pulsed (Note 1)	968	Α
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		961	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6	V/ns
P _D F	Power Dissipation	(T _C = 25 ^o C)	245	W
		- Derate Above 25°C	1.64	W/ºC
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

* Package limitation current is 120A

Thermal Characteristics

Symbol	Parameter	FDP023N08B_F102	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.61	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	0/10

November 2013

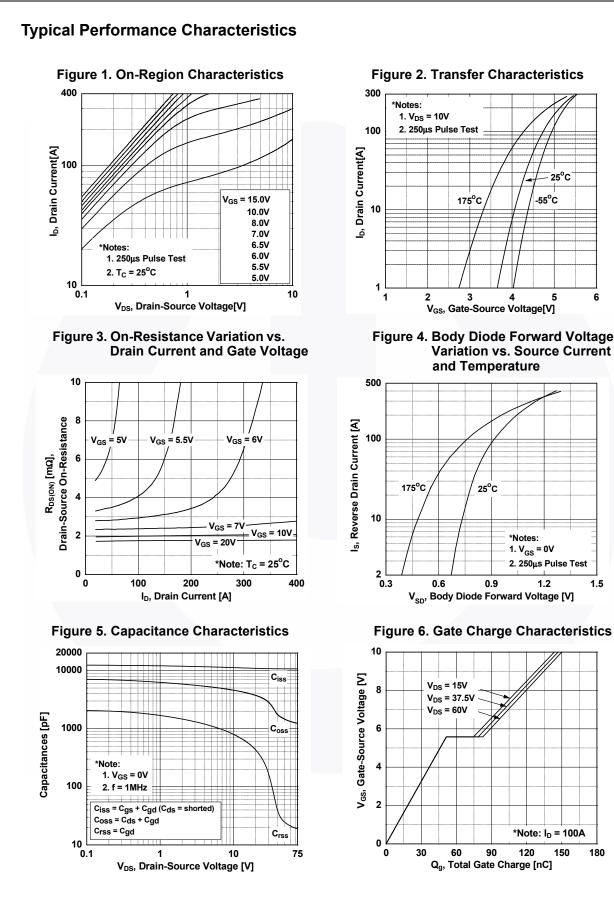
		Package	Packing Method	Reel Size	T	ape Width	Qua	antity	
		TO-220				N/A	50 units		
Electrica	l Chara	cteristics T _C =	= 25ºC unles	s otherwise noted.					
Symbol		Parameter		Test Conditio	ns	Min.	Тур.	Max.	Unit
Off Charac	teristics								
BV _{DSS}		Source Breakdown \	/oltage	I _D = 250 μA, V _{GS} = 0V, T _C = 25 ^o C		75	_	-	V
ΔBV_{DSS}		wn Voltage Temperat	-						
$/\Delta T_J$	Coefficie		uro	$I_D = 250 \ \mu$ A, Referenced to 25° C		-	0.35	-	V/°C
	7			V _{DS} = 60 V, V _{GS} = 0 V		-	-	1	
DSS	Zero Gat	e Voltage Drain Curr	Irrent $V_{DS} = 60 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$			-	-	500	μA
I _{GSS}	Gate to E	Body Leakage Currei	nt	$V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$		-	-	±100	nA
On Charac	teristics								
V _{GS(th)}		eshold Voltage		V _{GS} = V _{DS} , I _D = 250 μA		2.0	-	3.8	V
R _{DS(on)}		ain to Source On Re	sistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 75 \text{ A}$		-	1.96	2.35	mΩ
9FS	Forward Transconductance			$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 75 \text{ A}$		-	185	-	S
Dynamic C	haracto	ristics							
-			_				10350	13765	۳E
C _{iss}		pacitance		V _{DS} = 37.5 V, V _{GS} = 0 V, f = 1 MHz			1855	2465	pF
C _{oss}	-	apacitance	<u>^</u>			-	46.8	2405	pF
C _{rss}		Transfer Capacitanc		1/ - 275 1/ 1/ - 01	1		3290	-	pF
C _{oss(er)}		Related Output Capao e Charge at 10V	Silance	$V_{DS} = 37.5 \text{ V}, V_{GS} = 0 \text{ V}$		-	150	- 195	pF nC
Q _{g(tot)}		Source Gate Charge	_			-	50.3	195	nC
Q _{gs}		Drain "Miller" Charge		$V_{GS} = 10 V$	-,	-	31.7	-	nC
Q _{gd}		teau Volatge	-			-	4.9	-	V
V _{plateau}		e Charge Sync.		V _{DS} = 0 V, I _D = 50 A	(Note 4)		127.4	-	nC
Q _{sync}	Output C		-	$V_{DS} = 37.5 \text{ V}, V_{GS} = 0 \text{ V}$	1	-	146.2	-	nC
Q _{oss}	-			$v_{\rm DS} = 37.3 v, v_{\rm GS} = 0 v$		-	140.2	-	
Switching	Charact	eristics							
t _{d(on)}	Turn-On	Delay Time		V_{DD} = 37.5 V, I _D = 100 A, V _{GS} = 10 V, R _G = 4.7 Ω		-	41	92	ns
t _r	Turn-On	Rise Time				-	71	151	ns
t _{d(off)}		Delay Time				-	111	232	ns
t _f	Turn-Off	Fall Time			(Note 4)	-	56	122	ns
ESR	Equivaler	nt Series Resistance	(G-S)	f = 1 MHz		-	2.23	-	Ω
Drain-Sou	rce Diod	e Characteristic	s						
I _S		n Continuous Drain to		de Forward Current		-	-	242*	A
		Pulsed Drain to Sou				-	-	968	A
ISM									1
I _{SM} V _{SD}	Drain to S	Source Diode Forwar	d Voltage	$V_{GS} = 0 V$, $I_{SD} = 75 A$		-	-	1.3	V
V _{SD}		Source Diode Forwar Recovery Time	d Voltage	V _{GS} = 0 V, I _{SD} = 75 A V _{GS} = 0 V, V _{DD} =37.5 V,		-	- 79.3	1.3 -	V ns

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 3 mH, I_{AS} = 25.32 A, starting T_J = 25°C.

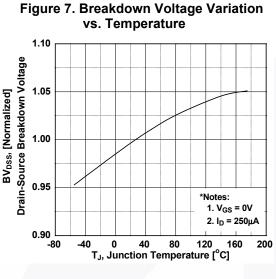
3. $I_{SD} \le 100 \text{ A}$, di/dt $\le 200 \text{ A/}\mu\text{s}$, $V_{DD} \le \text{BV}_{DSS}$, starting $\text{T}_{\text{J}} = 25^{\circ}\text{C}$. 4. Essentially independent of operating temperature typical characteristics.

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Typical Performance Characteristics (Continued)





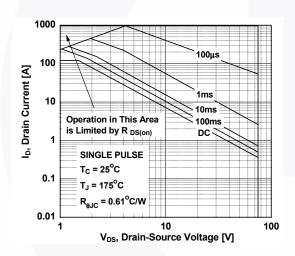
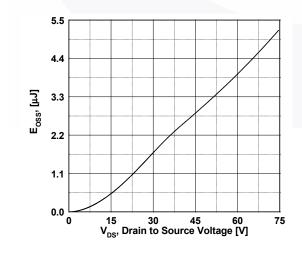
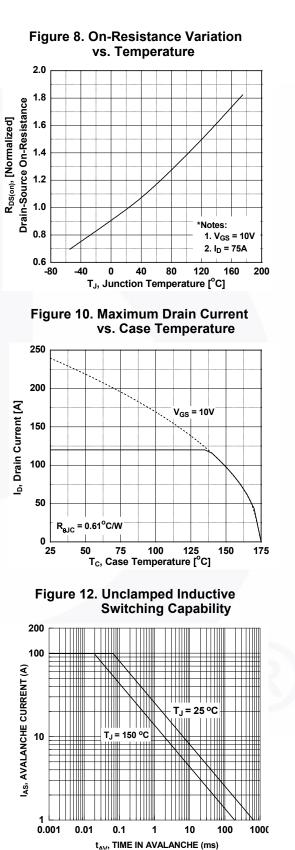


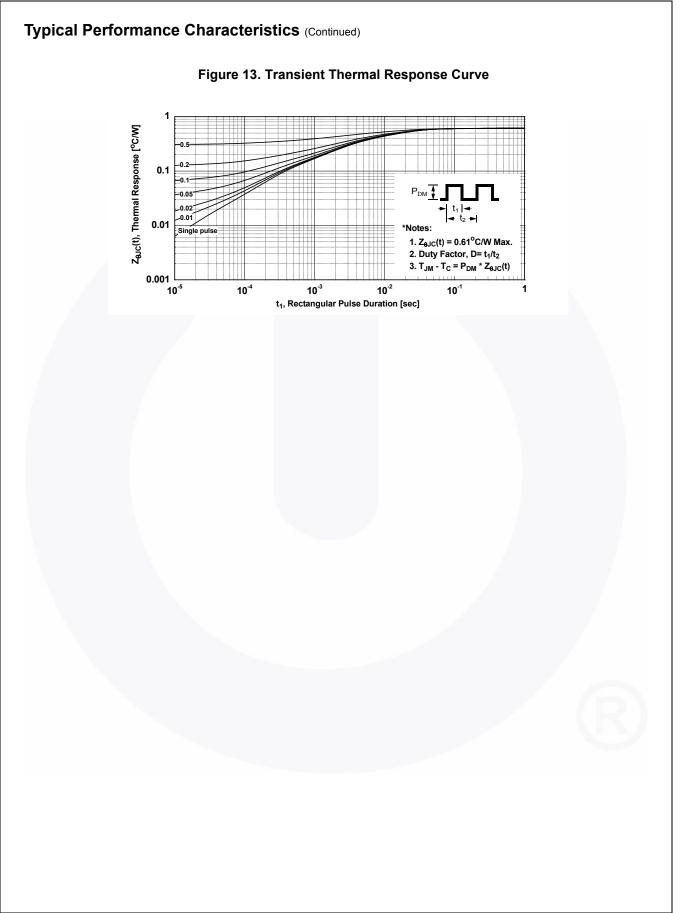
Figure 11. Eoss vs. Drain to Source Voltage

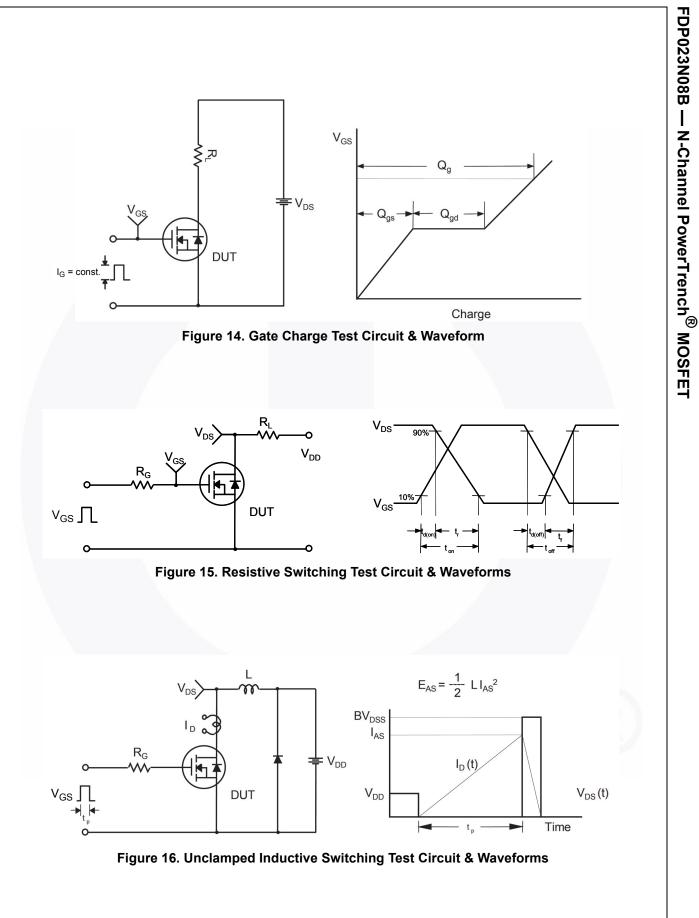




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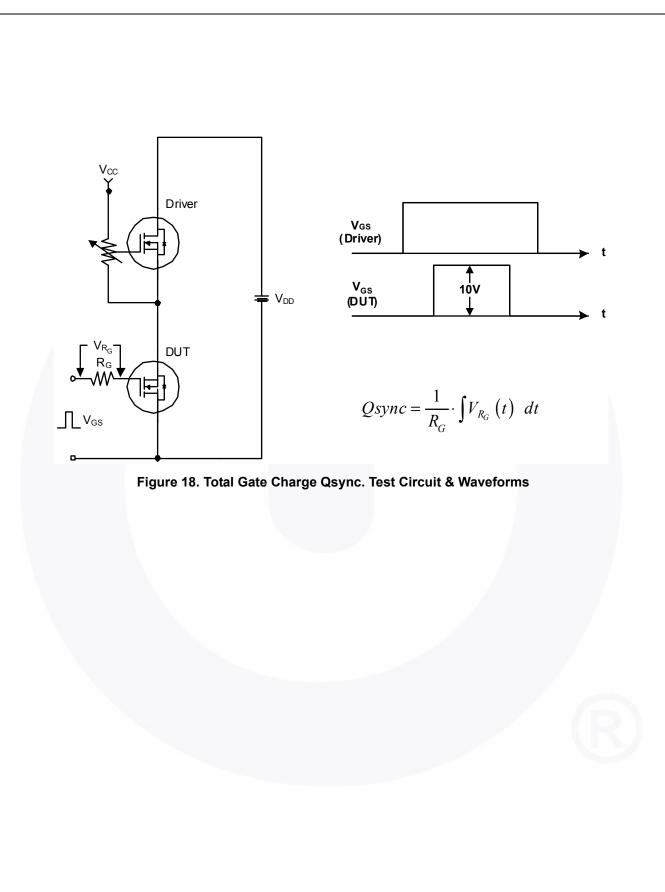


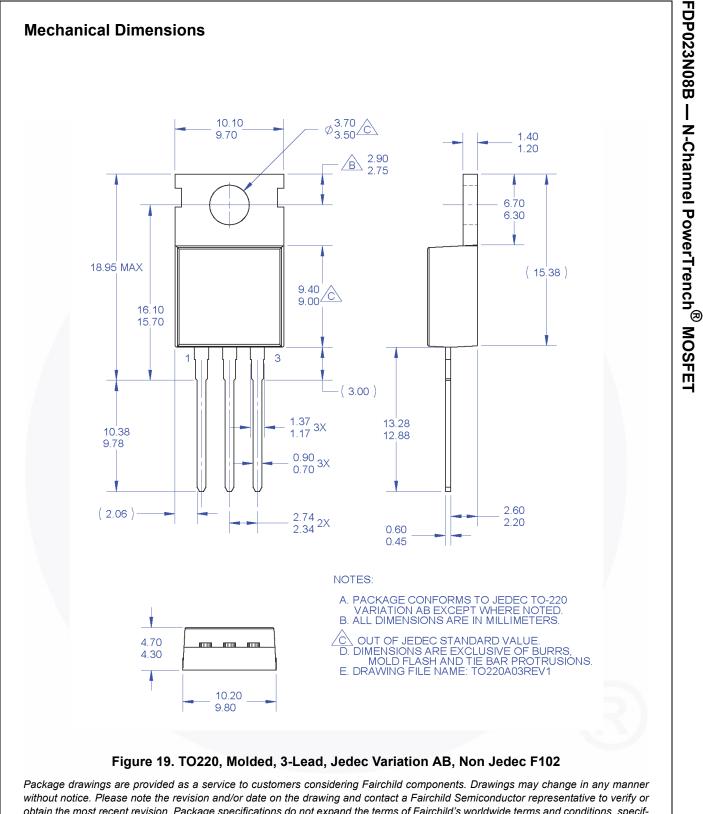


DUT + v_{DS} a ۱_{SD} م L Driver R_G, Same Type as DUT L F ∨_{DD} $\prod V_{GS}$ • dv/dt controlled by R_G • I_{SD} controlled by pulse period Î Gate Pulse Width V_{GS} D = Gate Pulse Period 10V (Driver) I_{FM}, Body Diode Forward Current I _{SD} di/dt (DUT) I_{RM} Body Diode Reverse Current V_{DS} (DUT) Body Diode Recovery dv/dt V_{SD} V_{DD} Body Diode Forward Voltage Drop Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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